# Topological phase transition in 3D noncentrosymmetic systems

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### Reference

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- <u>B. -J. Yang</u>, M. S. Bahramy, R. Arita, H. Isobe, E.-G. Moon and N. Nagaosa, Phys. Rev. Letts. 110, 086402 (2013).
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# <u>Outline</u>

#### 1. Accidental band crossing and topological phase transition

- Introduction to 3D topological insulators.
- Topological phase transition via accidental band touching
- <u>Direct topological transition</u> between two insulators

#### 2. (Direct) topological phase transition in BiTeI

- Topological phase transition of pressured BiTeI (First-principle cal.)
- Unusual band dispersion near the quantum critical point
- Physical properties at the quantum critical point

## 3D topological insulator

<u>3D narrow gap semi-conductors with 2D helical Dirac metal on the surface</u>



#### <u>Topologcal stability of the surface states</u>: bulk gap and time-reversal symmetry

## Topological phase transition

#### Accidental band crossing

A single tuning parameter : P



Accidental band crossing is not easy to achieve !

# Conditions for accidental band crossing



(2) Dimensionality : total number of parameters (N<sub>P</sub>) of  $\Psi(\mathbf{k}, P)$ 

(i)  $N_P = 3$  in 2D (kx,ky,P), (ii)  $N_P = 4$  in 3D (kx,ky,kz,P)

Accidental band crossing is possible for  $N_P \ge D_C$ 

## Phase diagram in 3D noncentrosymmetric



## <u>Lattice structure of BiTeI</u>

• BiTeI : polar layered semiconductor



# Bulk band structure : Rashba spin-splitting



Rashba spin splitting in bulk bands !

## Topological phase transition under pressure

Energy spectrum E(k<sub>x</sub>,k<sub>y</sub>;z) of a system with finite length along the z-direction



Spin helicity of the top and bottom surface states are the same !
 cf) Inversion symmetric TI : opposite spin helicity

## Direct insulator-insulator transition



cf) Generic phase diagram in 3D noncentrosymmetric systems



## Band crossing in 3D non-centrosymmetric systems

Ρ



$$H= f_{0} + f_{1}\sigma_{1} + f_{2}\sigma_{2} + f_{3}\sigma_{3}$$

$$E_{conduction} = f_{0} + (f_{1}^{2} + f_{2}^{2} + f_{3}^{2})^{1/2},$$

$$E_{valence} = f_{0} - (f_{1}^{2} + f_{2}^{2} + f_{3}^{2})^{1/2}$$

$$\frac{f_{1}(k_{x}, k_{y}, k_{z}, P) = 0}{f_{2}(k_{x}, k_{y}, k_{z}, P) = 0}$$

$$f_{3}(k_{x}, k_{y}, k_{z}, P) = 0$$

One free parameter !





## Intermediating semi-metallic states



$$\mathsf{H=} (\mathbf{v}_1 \cdot \mathbf{k}) \sigma_1 + (\mathbf{v}_2 \cdot \mathbf{k}) \sigma_2 + (\mathbf{v}_3 \cdot \mathbf{k}) \sigma_3$$

Chiral charge =  $\frac{\mathbf{v}_1 \cdot (\mathbf{v}_2 \times \mathbf{v}_3)}{|\mathbf{v}_1 \cdot (\mathbf{v}_2 \times \mathbf{v}_3)|}$ 

## How to achieve a direct transition?

1. Zero chiral charge at the critical point



2. Small number of constraints :  $N_{Parameter} = 4 > N_{Constraint} = 3$ 

H= 
$$f_0 + f_1\sigma_1 + f_2\sigma_2 + f_3\sigma_3$$

Impose additional constraint from crystalline symmetry ! ( $N_c \rightarrow N_c + 1$ )

Add 
$$f_4 (k_x, k_y, k_z, P) = 0$$

## <u>Constraint from crystalline symmetry</u>



Conduction band:  $H_{c}(k) = \frac{k_{x}^{2} + k_{y}^{2}}{2m_{\perp,c}^{*}} + \frac{(k_{z} - \pi/c)^{2}}{2m_{\parallel,c}^{*}} + \frac{v_{k,c}(k_{x}\sigma_{y} - k_{y}\sigma_{x})}{Rashba} + \frac{\lambda_{c}\left(3k_{x}^{2} - k_{y}^{2}\right)k_{y}\sigma_{z}}{Warping}$ 

## Evidence for direct insulator-insulator transition



### Unusual properties at the quantum critical point

$$H_{\rm QCP}(\mathbf{p}) = A p_1^2 \tau_1 + v p_2 \tau_2 + v p_3 \tau_3,$$

1. Unusual temperature dependence



2. Anisotropic DC conductivity :  $\sigma_{11}$  /  $\sigma_{33} \propto$  T

(1) Coulomb scattering (e-e interaction):  $\frac{1}{\tau} = \alpha^2 T$  with  $\alpha = \frac{e^2}{4\pi\varepsilon v}$  $\sigma_{11}(T) \propto T^{3/2} \quad \sigma_{22,33}(T) \propto T^{1/2}$ 

(2) Disorder scattering (Born approx.):  $\frac{1}{\tau(w)} \approx 2\pi\gamma_0 D(w)$  with  $\gamma_0 = \frac{n_i V_0^2}{2}$  $\sigma_{11} \propto T$ ,  $\sigma_{22,33} = \text{const.}$ 



 $\frac{g^2}{q_1^2 + na^{3/2}}$ 

 $V_{\rm screened}({f q}) \sim$ 

0 0.2 0.4 0.6 0.8 OL

Anisotropic screened Coulomb interaction !

### <u>Summary</u>

1. Generic phase diagram of 3D non-centrosymmetric system achievable via accidental band crossing



- 2. Direct insulator-insulator transition due to crystalline symmetry
- 3. Anisotropic dispersion at the critical point



4. Unusual thermodynamic properties and anisotropic transport properties

## Fate of semi-metallic phase

• Semi-metal phase has topological stability !



## Spin-orbit coupling induced band inversion

#### Searching for new topological insulators

 Guiding principle: spin-orbit coupling induced band inversion (parity exchange through accidental band crossing)



(H. Zhang et al., Nat. Phys. (2009))

#### Conditions for the direct insulator-insulator transition

• Away from the critical point ( $m < m_c$  and  $m > m_c$ ):

Conduction and valence bands should have an extremum !



Condition for the direct transition
 The location of the extremum should move along a straight line.

#### Anisotropic dispersion at the quantum critical point

• Anisotropic dispersion at QCP : direct consequence of zero chiral charge



Cf) Weyl semi-metal D(E)  $\propto$  E<sup>2</sup>, Quadratic band dispersion D(E)  $\propto$  E<sup>1/2</sup>